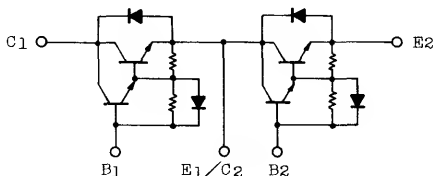


HIGH POWER SWITCHING APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

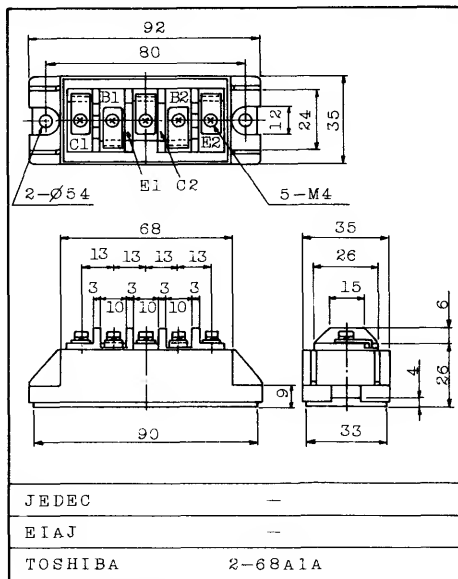
FEATURES:

- . The Collector is Isolated from Case.
- . 2 Power Transistors and 2 Free Wheeling Diodes are Built-in to 1 Package.
- . High DC Current Gain : $h_{FE}=100(\text{Min.})$ ($I_C=50\text{A}$)
- . Low Saturation Voltage: $V_{CE(\text{sat})}=2\text{V}(\text{Max.})$ ($I_C=50\text{A}$)
- . High Speed : $t_f=2\mu\text{s}(\text{Max.})$ ($I_C=50\text{A}$)

EQUIVALENT CIRCUIT



Unit in mm



Weight : 210g

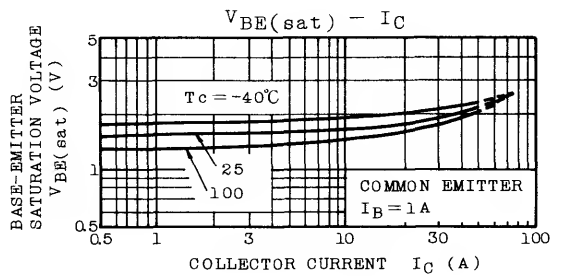
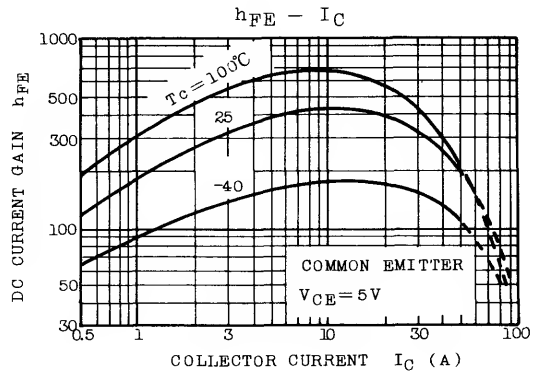
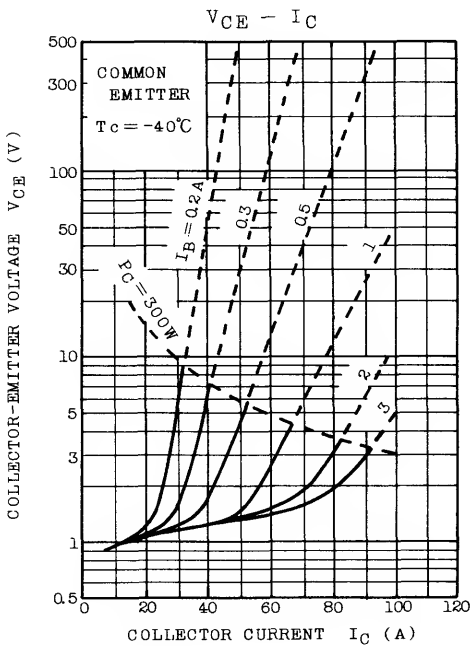
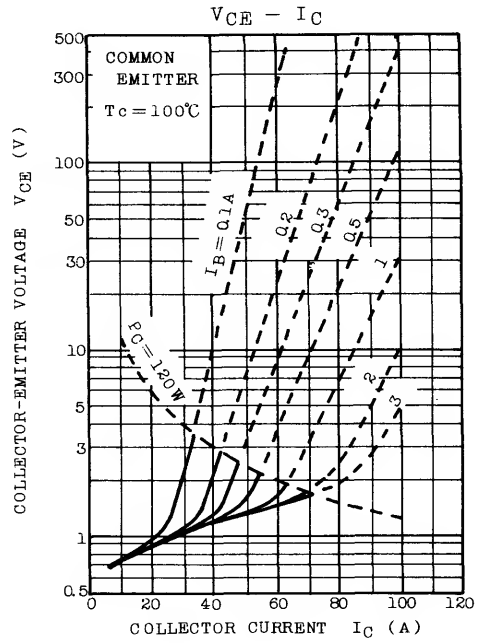
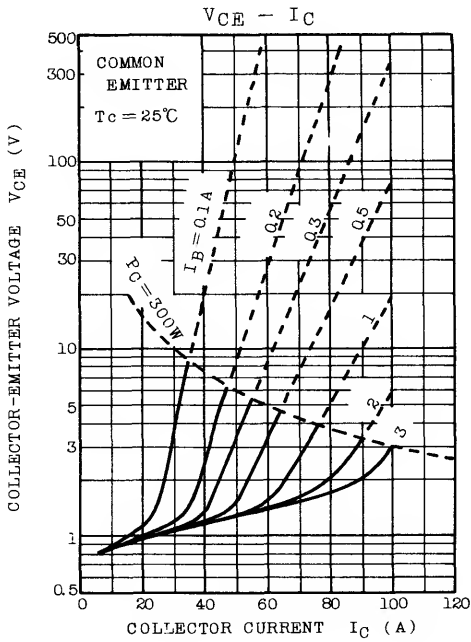
MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	600	V
Collector-Emitter Voltage	V_{CE0}	600	V
Collector-Emitter Sustaining Voltage	$V_{CE0(\text{SUS})}$	450	V
Emitter-Base Voltage	V_{EB0}	6	V
Collector Current	DC	I_C	50
	lms	I_C	100
	DC	$-I_C$	50
Base Current	I_B	3	A
Collector Power Dissipation ($T_c=25^\circ\text{C}$)	P_C	300	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 ~ 125	$^\circ\text{C}$
Isolation Voltage	V_{Isol}	2000 (AC 1 Minute)	V
Screw Torque (Terminal/Mounting)		20/30	kg·cm

MG50G2CL3

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} =600V, I _E =0	-	-	1.0	mA
Emitter Cut-off Current		IEBO	VEB=6V, IC=0	-	-	200	mA
Collector-Emitter Sustaining Voltage		V _{CEO(SUS)}	IC=0.5A, L=40mH	450	-	-	V
DC Current Gain		h _{FE}	V _{CE} =5V, IC=50A	100	-	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	IC=50A, IB=1A	-	-	2.0	V
Base-Emitter Saturation Voltage		V _{BE(sat)}		-	-	2.5	V
Emitter-Collector Voltage		V _{ECO}	IE=50A, IB=0	-	-	1.5	V
Reverse Recovery Time		t _{rr}	-IC=50A, VEB=3V VCE=300V	-	-	2.0	μs
Collector Output Capacitance		C _{ob}	V _{CB} =50V, IE=0, f=1MHz	-	520	-	pF
Switching Time	Turn-on Time	t _{on}	<p>50μs INPUT I_{B1} I_{B2} OUTPUT I_{B1} I_{B2} C_c V_{CC}=300V</p>	-	-	1.0	μs
	Storage Time	t _{stg}		-	-	12	
	Fall Time	t _f		I _{B1} =-I _{B2} =1A DUTY CYCLE=0.5%	-	-	
Thermal Resistance (Junction to Case)		R _{th(j-c)}	Transistor	-	-	0.41	°C/W
			Diode	-	-	1.3	



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